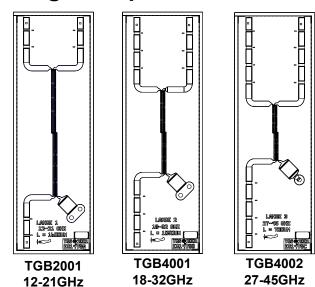


Lange Coupler Set



Preliminary Measured Data

TGB2001

-2

Product Data Sheet Aug 5, 2008 **TGB2001 TGB4001 TGB4002**

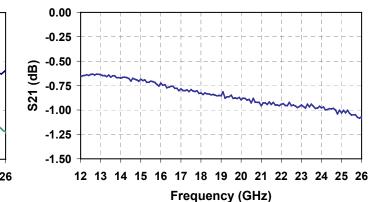
Key Features and Performance

- Very Low Loss (<0.25dB Typical)
- High Power 1W 50Ω Termination
- Broadband 3dB Power Split
- Chip dimensions: 1.0 x 3.0 x 0.1 mm (40 x 120 x 4 mils)
- 3 sizes Cover 12GHz 45GHz

TGB2001 Back-to-Back

Primary Applications

Power Combining



Direct Coupled -3 S21 (dB) -5 12 13 14 15 16 17 18 19 20 21 22 23 24 25 26 Frequency (GHz)

Note: Datasheet is subject to change without notice.



Product Data Sheet

TGB2001 TGB4001 TGB4002

TABLE I MAXIMUM RATINGS

Symbol	Parameter 1/	Value	Notes
P _{IN}	Input Continuous Wave Power	TBD dBm	
Τ _M	Mounting Temperature	320 ⁰ C	
	(30 Seconds)		
T _{STG}	Storage Temperature	-65 to 150 ⁰ C	

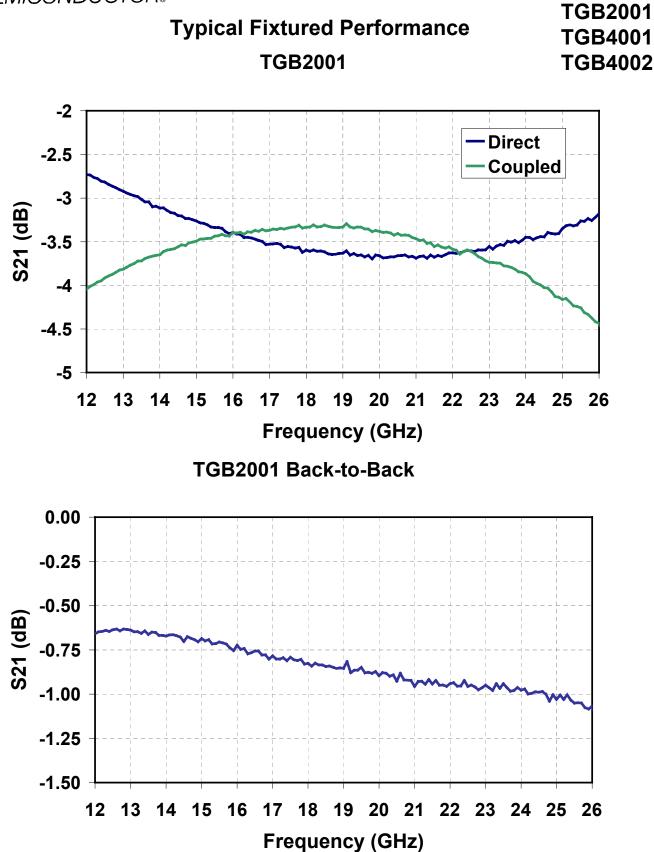
1/ These ratings represent the maximum operable values for this device.

—

TriQuint Semiconductor Texas Phone : (972)994-8465 Fax: (972)994-8504 Web: www.triquint.com

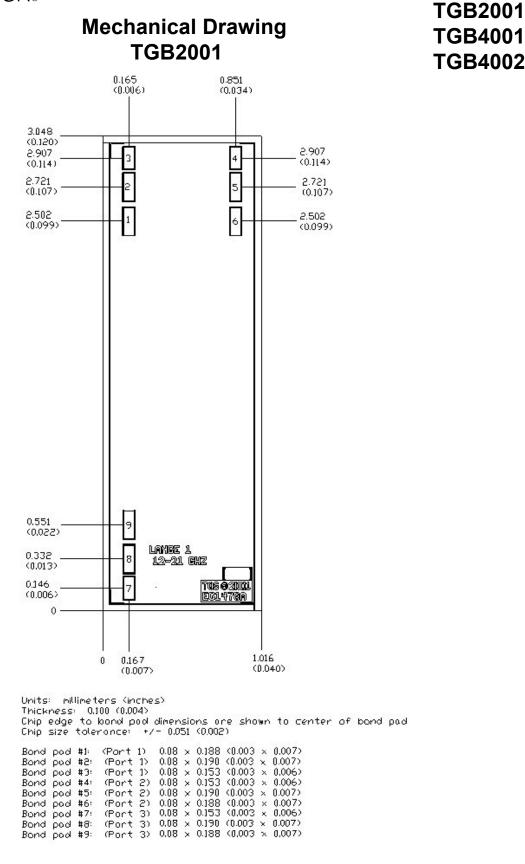
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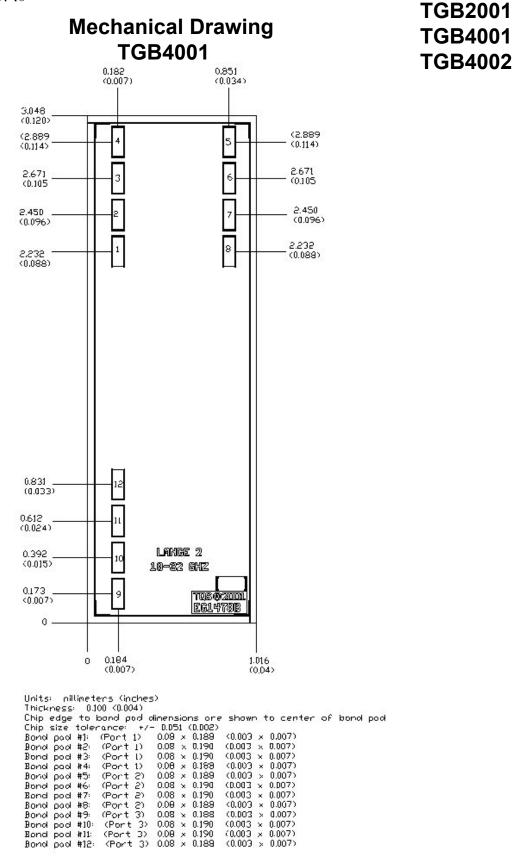
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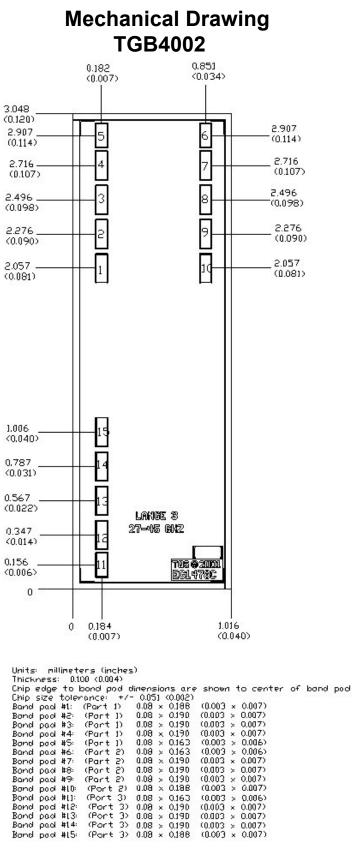


TGB2001

TGB4001

TGB4002







TGB2001 TGB4001 TGB4002

Assembly Process Notes

Reflow process assembly notes:

- Use AuSn (80/20) solder with limited exposure to temperatures at or above 300°C. (30 seconds maximum)
- An alloy station or conveyor furnace with reducing atmosphere should be used.
- No fluxes should be utilized.
- Coefficient of thermal expansion matching is critical for long-term reliability.
- Devices must be stored in a dry nitrogen atmosphere.

Component placement and adhesive attachment assembly notes:

- Vacuum pencils and/or vacuum collets are the preferred method of pick up.
- Air bridges must be avoided during placement.
- The force impact is critical during auto placement.
- Organic attachment can be used in low-power applications.
- Curing should be done in a convection oven; proper exhaust is a safety concern.
- Microwave or radiant curing should not be used because of differential heating.
- Coefficient of thermal expansion matching is critical.

Interconnect process assembly notes:

- Thermosonic ball bonding is the preferred interconnect technique.
- Force, time, and ultrasonics are critical parameters.
- Aluminum wire should not be used.
- Discrete FET devices with small pad sizes should be bonded with 0.0007-inch wire.
- Maximum stage temperature is 200°C.

GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.

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